$_{CES}$	Collector-emitter voltage	650	V
$_{GES}$	Gate-emitter voltage	±20	V
$_{C}$	Continuous collector current ($_{C}$=25)	30	A
	Continuous collector current ($_{C}$=100)	15	A
$_{CM}$	Pulsed collector current, $_{p}$ limited by $_{vjmax}$	60	A
$_{F}$	Diode continuous forward current ($_{C}$=100)		

$_{CES}$	Collector-emitter breakdown voltage	$_{GE}$=0V, $_{C}$=250μA	650	-	-	V
$_{CES}$	Collector-emitter leakage current	$_{CE}$=650V, $_{GE}$=0V	-	-	50	μA
$_{GES}$	Gate leakage current, forward	$_{GE}$=20V, $_{CE}$=0V	-	-	100	nA
	Gate leakage current, reverse	$_{GE}$=-20V, $_{CE}$=0V	-	-	-100	nA

Switching characteristics

$t_{d(on)}$	Turn-on delay time	V_{CC}=400V V_{GE}=0/15V I_C=15A R_G=10 Inductive load	-	15	-	ns
t_r	Rise time		-	17	-	ns
$t_{d(off)}$	Turn-off delay time		-	110	-	ns
t_f	Fall time		-	73	-	ns
E_{on}	Turn-on energy		-	0.38	-	mJ
E_{off}	Turn-off energy		-	0.37	-	mJ
E_{ts}	Total switching energy		-	0.75	-	mJ
$t_{d(on)}$	Turn-on delay time	V_{CC}=400V V_{GE}=0/15V I_C=15A R_G=10 Inductive load T_{vj}=175	-	14	-	ns
t_r	Rise time		-	18	-	ns
$t_{d(off)}$	Turn-off delay time		-	146	-	ns
t_f	Fall time		-	158	-	ns
E_{on}	Turn-on energy		-	0.44	-	mJ
E_{off}	Turn-off energy		-	0.64	-	mJ
E_{ts}	Total switching energy		-	1.08	-	mJ

($_{vj}$=25 unless otherwise specified)

$_{F}$	Diode forward voltage	$_{F}$=15A	-	1.4	-	V
		$_{F}$=15A, $_{vj}$=175	-	1.1	-	V
$_{rr}$	Diode reverse recovery time	$_{R}$=400V $_{F}$=15A d $_{F}$/d =-600A/μs	-	55	-	ns
$_{rrm}$	Diode peak reverse recovery current		-	9.5	-	A
$_{rr}$	Diode reverse recovery charge		-	220	-	nC
$_{rr}$	Diode reverse recovery time	$_{R}$=400V $_{F}$=15A d $_{F}$/d =-600A/μs $_{vj}$=175	-	77	-	ns
$_{rrm}$	Diode peak reverse recovery current		-	15	-	A
$_{rr}$	Diode reverse recovery charge		-	481	-	nC

A d c a c dad b c a d ca .



Fig 1. Typical output characteristic (vj=25)

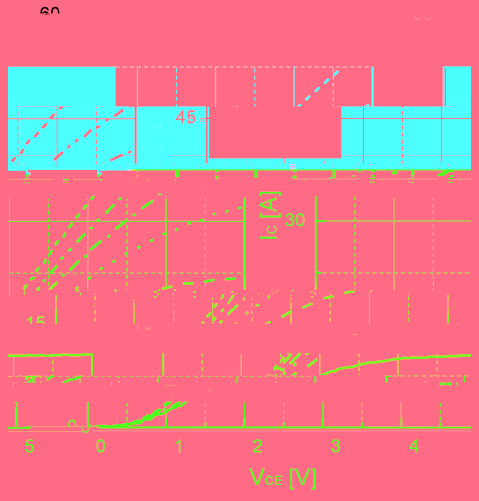


Fig 2. Typical output characteristic(vj=175)

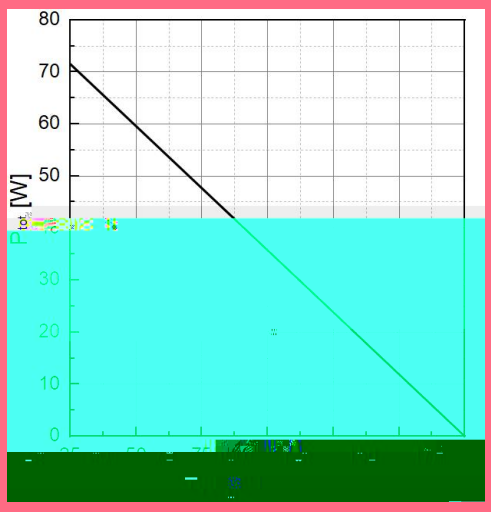


Fig 3. Power dissipation as a function of

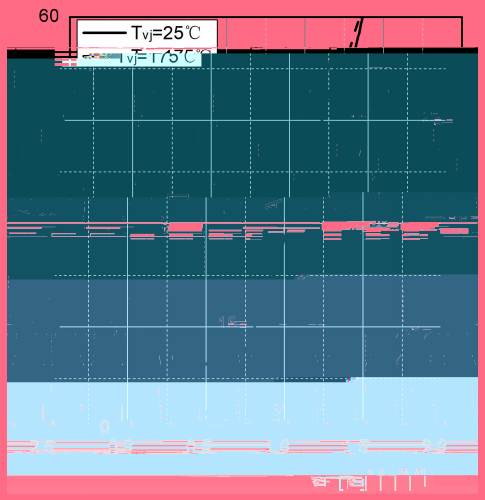


Fig 4. Typical F as a function of F

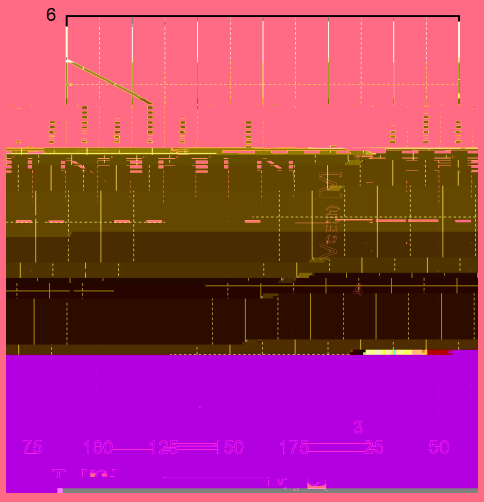


Fig 5. Typical GE(th) as a function of vj (C=1mA)

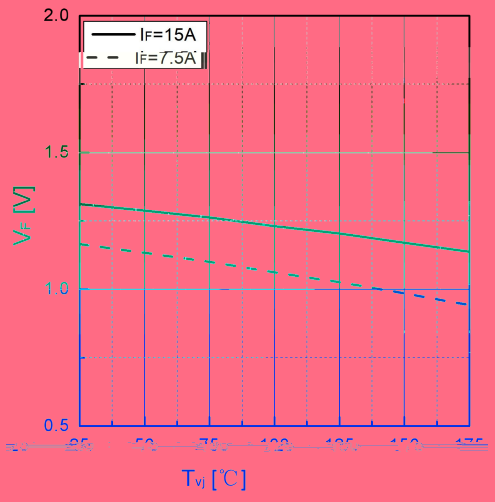


Fig 6. Typical F as a function of vj

A d c a c d a d b c a d c a .

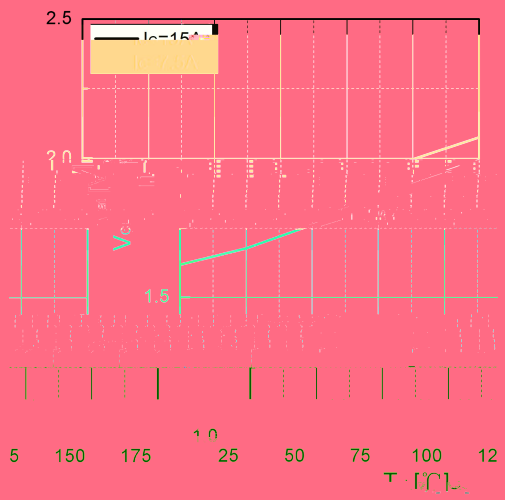


Fig 7. Typical $_{CEsat}$ as a function of $_{vj}$

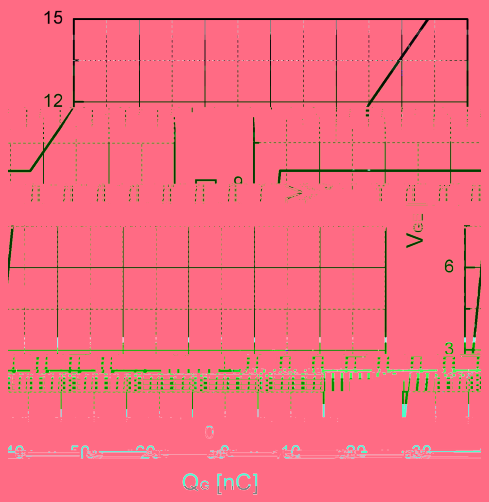


Fig 8. Typical Gate charge

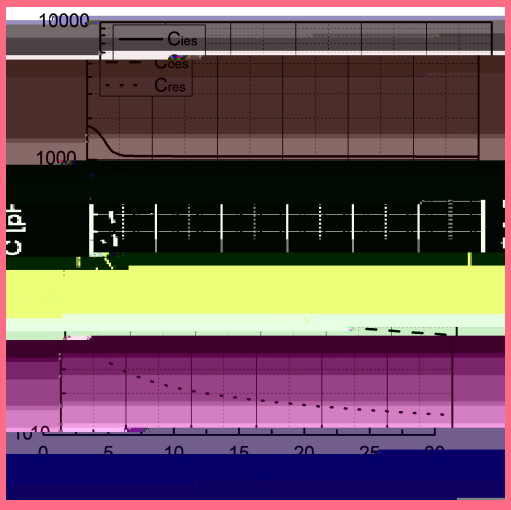


Fig 9. Typical capacitance as a function of $_{CE}$ (=1Mhz, $_{GE}$=0V)

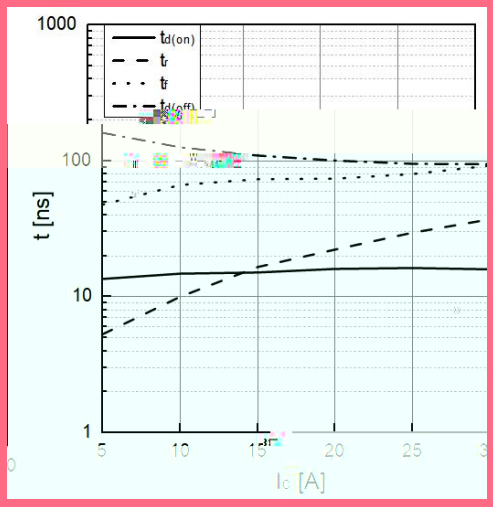


Fig 10. Typical switching times as a function of $_{C}$

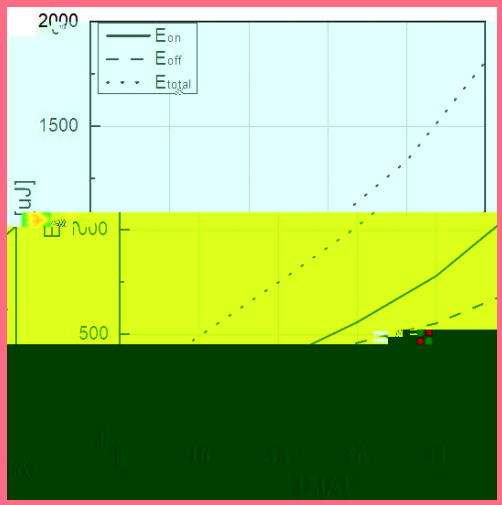


Fig 11. Typical switching energy losses as a function of $_{C}$

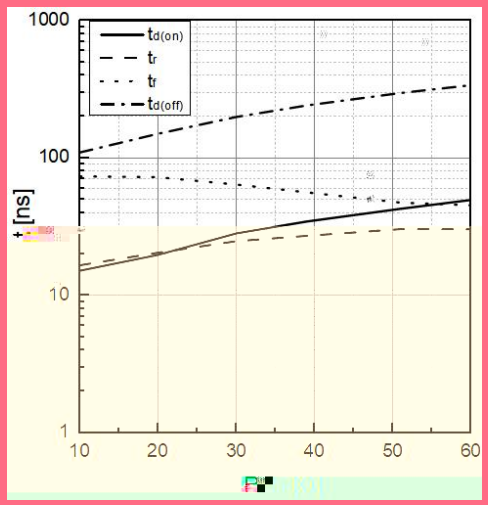


Fig 12. Typical switching times as a function of $_{G}$

A d c a c d a d b c a d c a .

A d c a c dad b c ad ca .

Dimensions						
Ref.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50	-	4.90	0.177	-	0.193
B	0.74 4	0.80	0.83	0.029	0.031	0.033

A d c a c dad b c ad ca .

Date	Revision	Changes
2023-11-27	Rev 1.1	Update
2024-03-18	Rev 1.2	Update
2025-04-08	Rev 1.3	Character Update
2026-06-24	Rev 1.4	Update thermal

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